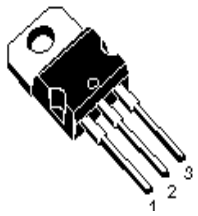
STP5NK65Z

N-CHANNEL 650V - 1.5Ω - 5A TO-220
Zener-Protected SuperMESH™Power MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D	Pw
STP5NK65Z	650 V	< 1.8 Ω	5 A	85 W

- TYPICAL $R_{DS}(on)$ = 1.5 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- IMPROVED ESD CAPABILITY
- 100% AVALANCHE RATED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY

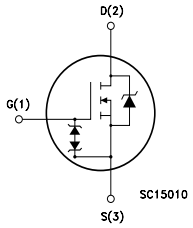


TO-220

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES, ADAPTORS AND PFC

Obsolete Product(s) - Obsolete Product(s)

ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP5NK65Z	P5NK65Z	TO-220	TUBE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	650	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	650	V
V_{GS}	Gate- source Voltage	± 30	V
I_D	Drain Current (continuous) at T_C = 25°C	5	A
I_D	Drain Current (continuous) at T_C = 100°C	3.1	A
I_{DM} (•)	Drain Current (pulsed)	20	A
P_{TOT}	Total Dissipation at T_C = 25°C	85	W
	Derating Factor	0.6	W/°C
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5KΩ)	2000	V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5	V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150 -55 to 150	°C °C

(•) Pulse width limited by safe operating area
(1) $I_{SD} \leq 5A$, di/dt ≤100 µA, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX.}$
(*) Limited only by maximum temperature allowed

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.64	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	50	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	4.2	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	190	mJ

GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	Igs=± 1mA (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to souce. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

Obsolete Product(s) - Obsolete Product(s)

ELECTRICAL CHARACTERISTICS (TCASE =25°C UNLESS OTHERWISE SPECIFIED)

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0	650			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125 °C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 50µA	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 2.1 A		1.5	1.8	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} = 10 V, I_D = 2.1 A		5		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		680 80 17		pF pF pF
$C_{oss\ eq.}$ (3)	Equivalent Output Capacitance	V_{GS} = 0V, V_{DS} = 0V to 480 V		98		pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 325 V, I_D = 2.1 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		20 15		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 520V, I_D = 4.2 A, V_{GS} = 10V		25 4.4 13.7	35	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 325 V, I_D = 2.1 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		140 40		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 520 V, I_D = 4.2 A, R_G = 4.7Ω, V_{GS} = 10V (Inductive Load see, Figure 5)		12 7 15		ns ns ns

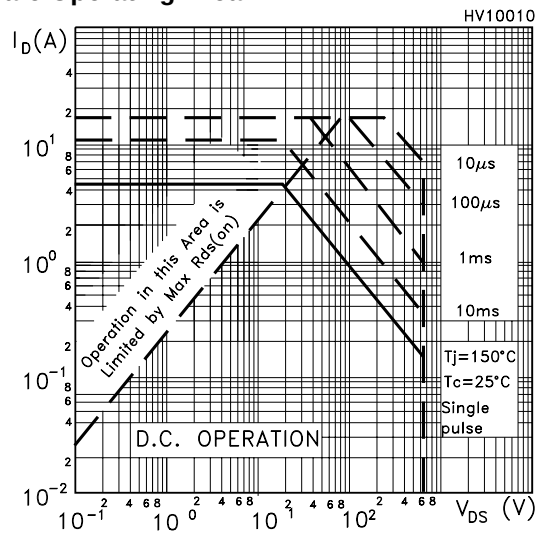
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				5 20	A A
V_{SD} (1)	Forward On Voltage	I_{SD} = 5 A, V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 4.2 A, di/dt = 100A/µs V_{DD} = 100V, T_j = 150°C (see test circuit, Figure 5)		375 1.76 10		ns µC A

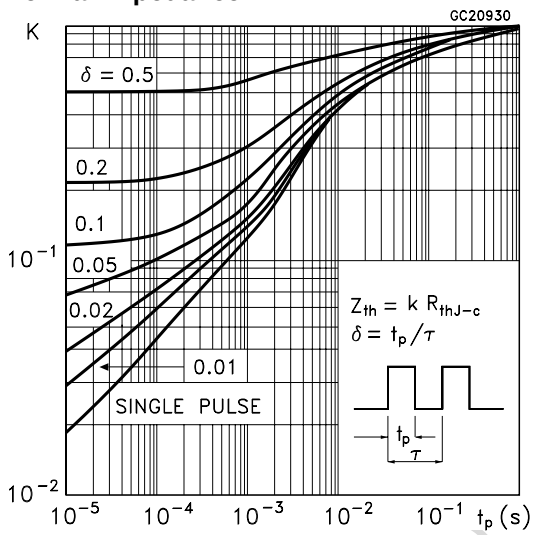
Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.
3. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Obsolete Product(s) - Obsolete Product(s)

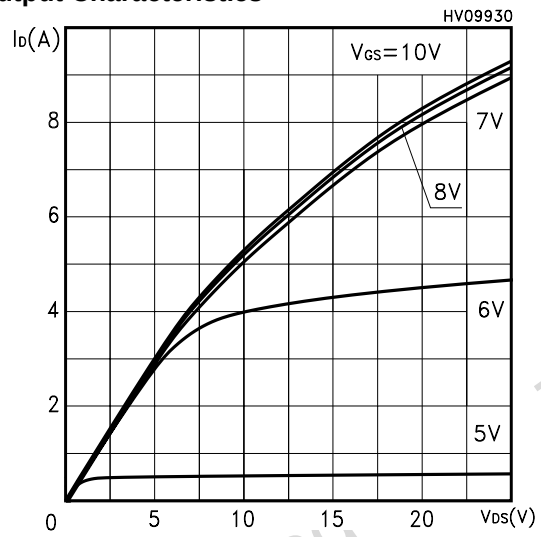
Safe Operating Area



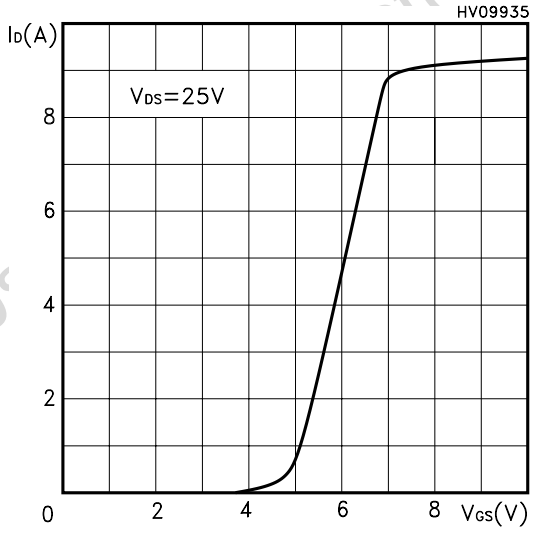
Thermal Impedance



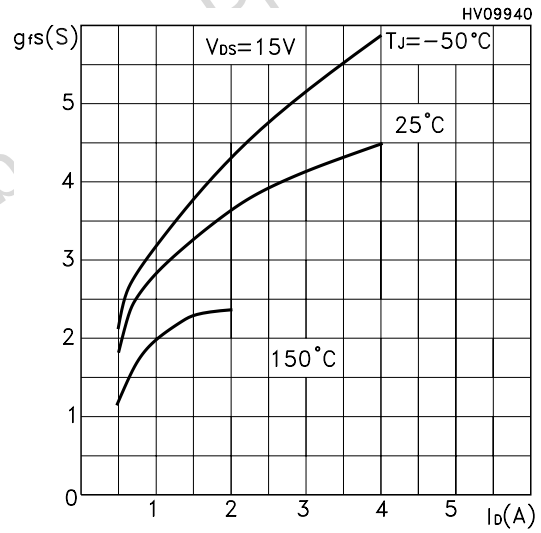
Output Characteristics



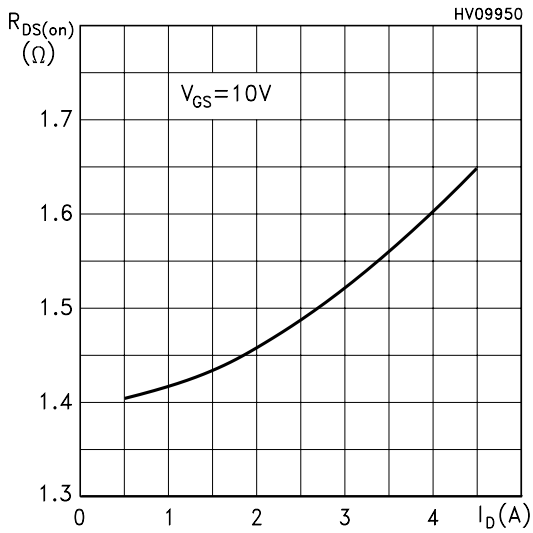
Transfer Characteristics



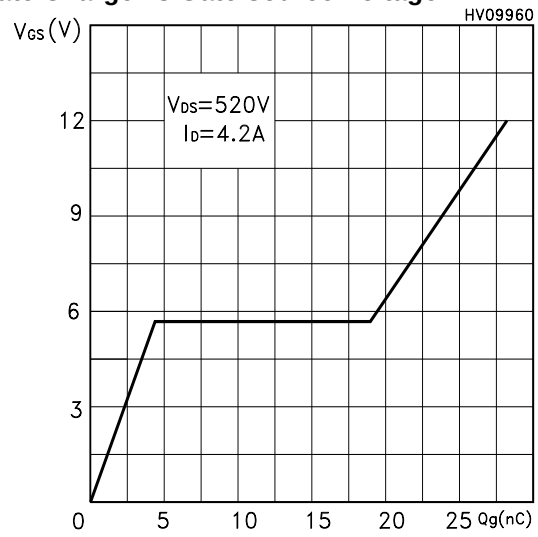
Transconductance



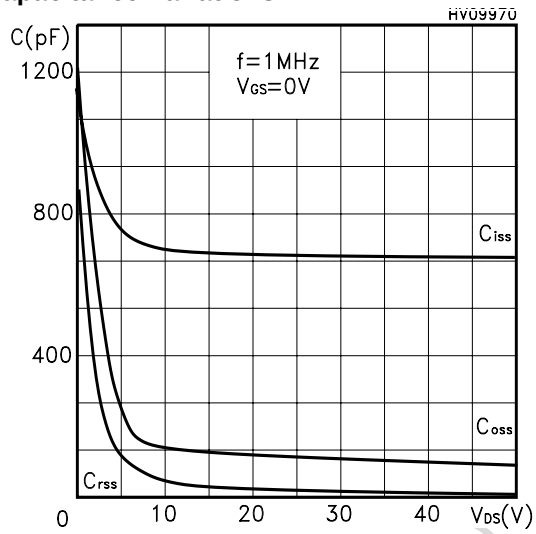
Static Drain-source On Resistance



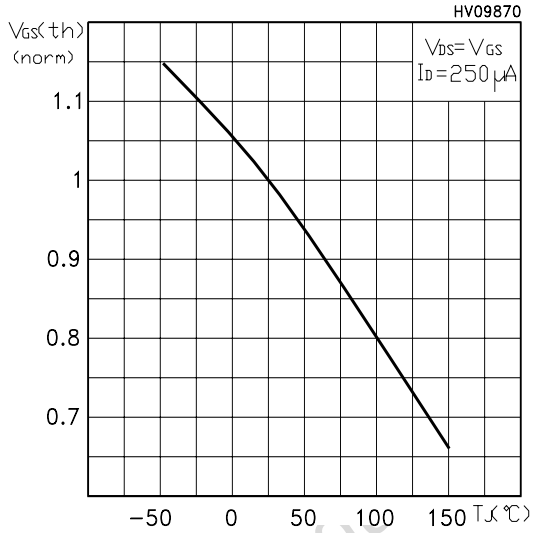
Gate Charge vs Gate-source Voltage



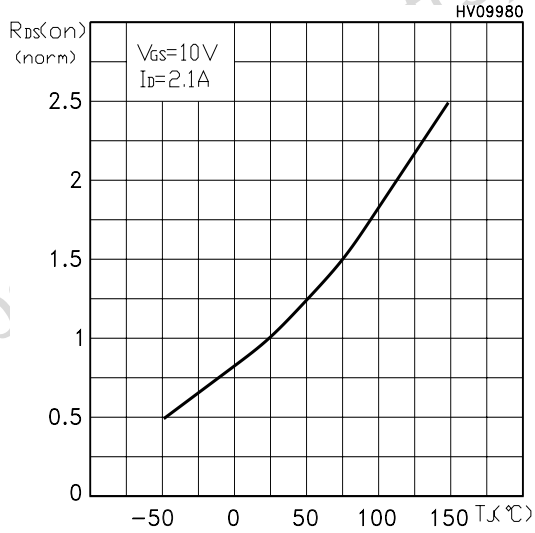
Capacitance Variations



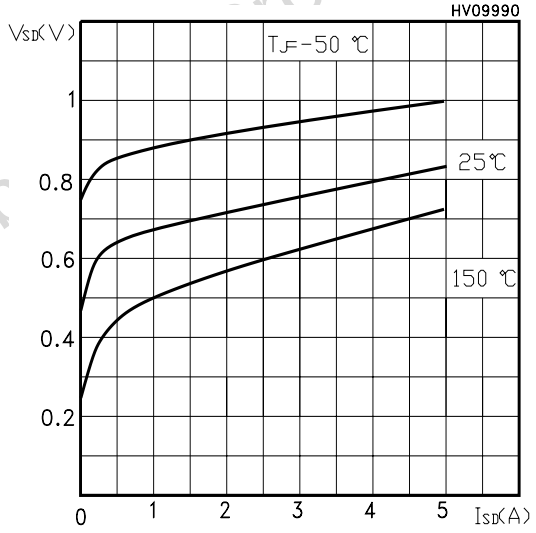
Normalized Gate Threshold Voltage vs Temp.



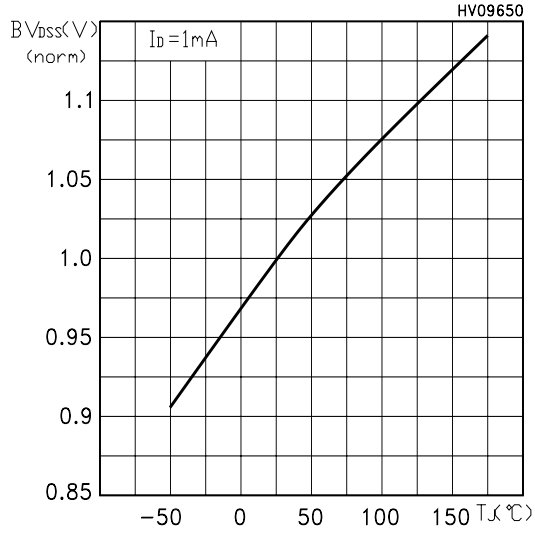
Normalized On Resistance vs Temperature



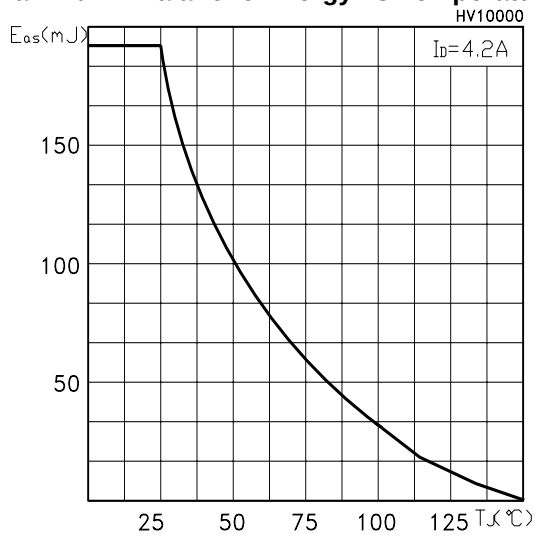
Source-drain Diode Forward Characteristics



Normalized BVDSS vs Temperature



Maximum Avalanche Energy vs Temperature



Obsolete Product(s) - Obsolete Product(s)

Fig. 1: Unclamped Inductive Load Test Circuit

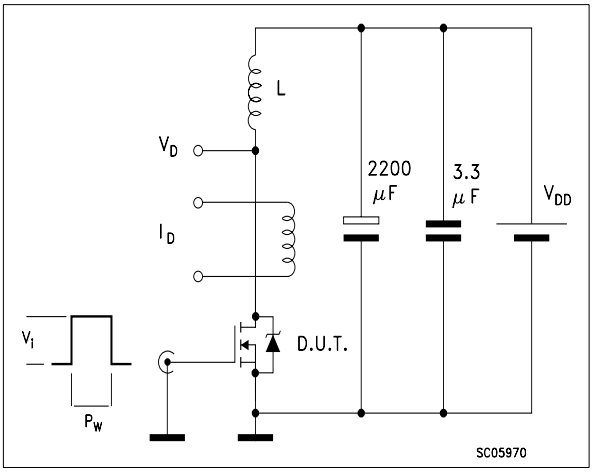


Fig. 2: Unclamped Inductive Waveform

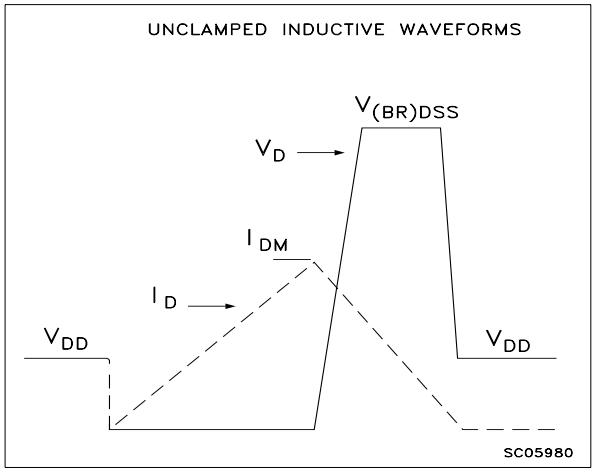


Fig. 3: Switching Times Test Circuit For Resistive Load

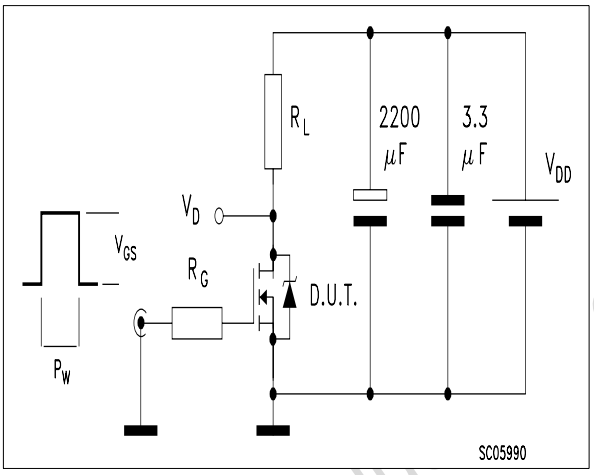


Fig. 4: Gate Charge test Circuit

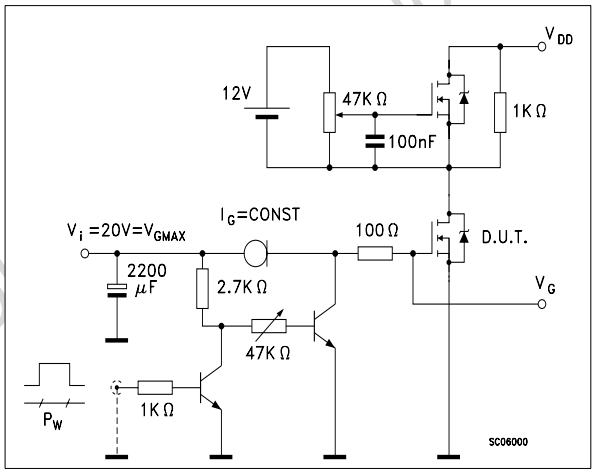
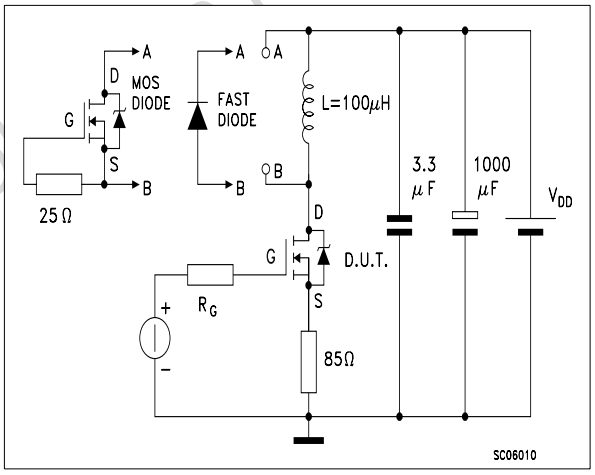
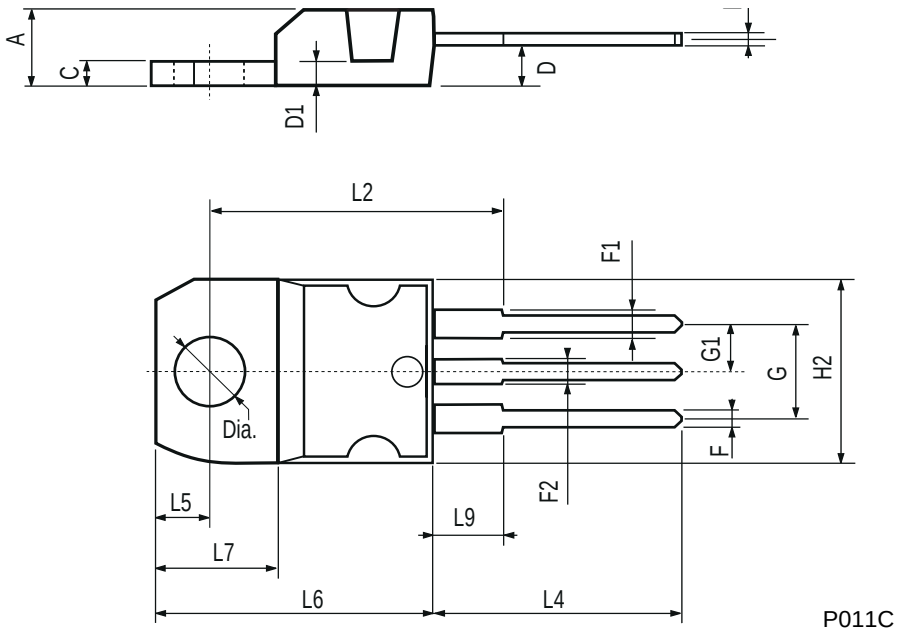


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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